Schottky Power Rectifier, Switch-Mode, 10 A, 45 V

MBRB1045G, MBRD1045G, SBRB1045G, SBRD81045T4G

This series of Power Rectifiers employs the Schottky Barrier principle in a large metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for use in low voltage, high frequency switching power supplies, free wheeling diodes, and polarity protection diodes.

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Short Heat Sink Tab Manufactured Not Sheared!
- SBRB and SBRD8 Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded, Epoxy Meets UL 94 V-0
- Weight: 1.7 grams for D²PAK (approximately) 0.4 grams for DPAK (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL1 Requirements
- ESD Ratings:
 - ◆ Machine Model = C (> 400 V)
 - Human Body Model = 3B (> 8000 V)



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SCHOTTKY BARRIER RECTIFIER 10 AMPERES, 45 VOLTS



MARKING DIAGRAM







A = Assembly Location
Y = Year
WW = Work Week
MBRB1045 = Device Code
G = Pb-Free Package
AKA = Diode Polarity

MARKING DIAGRAM





A = Assembly Location
 Y = Year
 WW = Work Week
 B1045 = Device Code
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MBRB1045G, MBRD1045G, SBRB1045G, SBRD81045T4G

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	45	٧
Average Rectified Forward Current, T _C = 135°C	I _{F(AV)}	10	Α
Peak Repetitive Forward Current (Square Wave, Duty = 0.5) T _C = 135°C	I _{FRM}	20	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	150 (MBRB/SBRB) 70 (MBRD/SBRD)	А
Operating Junction and Storage Temperature Range (Note 1)	T _J , T _{stg}	-65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance,			°C/W
(MBRB1045G)	_		
Junction-to-Case (Note 2)	$R_{\theta JC}$	1.0	
Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	50	
(MBRD1045G)			
Junction-to-Case (Note 2)	$R_{ hetaJC}$	2.43	
Junction-to-Ambient (Note 2)	$R_{\theta JA}$	68	

^{2.} When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 3)	V _F	0.57 0.72 0.84	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	IR	15 0.1	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRB1045G	D ² PAK-3	50 Units / Rail
SBRB1045G		50 Units / Rail
MBRB1045T4G	(Pb-Free)	800 Units / Tape & Reel
SBRB1045T4G	1	800 Units / Tape & Reel
MBRD1045G		50 Units / Rail
MBRD1045T4G	DPAK (Pb-Free)	2,500 Units / Tape & Reel
SBRD81045T4G		2,500 Units / Tape & Reel
SSBRD81045T4G		2,500 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

^{3.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%

MBRB1045G, MBRD1045G, SBRB1045G, SBRD81045T4G

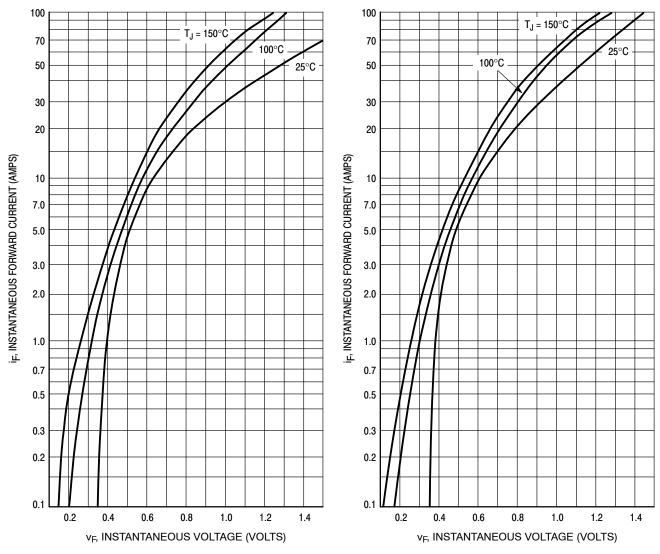


Figure 1. Maximum Forward Voltage

 $T_J = 150^{\circ}C$

125°C

100°C

75°C

25°C

100

10

1.0

REVERSE CURRENT (mA)

<u>څ</u>

0.01

0.001

5.0

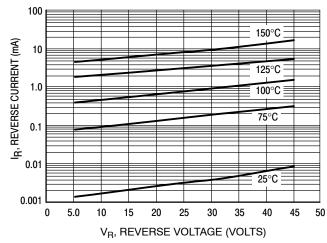


Figure 2. Typical Forward Voltage



MBRB1045G, MBRD1045G, SBRB1045G, SBRD81045T4G

1200

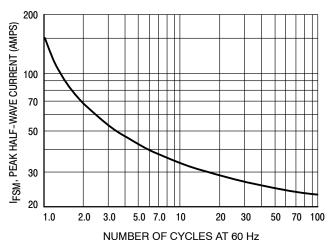


Figure 8. Maximum Surge Capability

Figure 5. Typical Capacitance

V_R, REVERSE VOLTAGE (VOLTS)

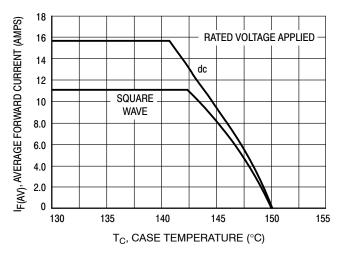


Figure 6. Current Derating, Case, $R_{\theta JC}$ = 1.0 °C/W

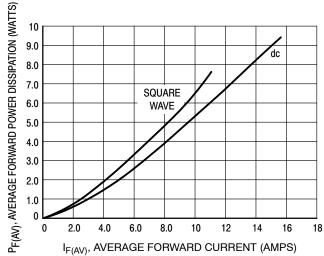


Figure 7. Forward Power Dissipation

DETAIL A BOTATED 90° CW

DPAK (SINGLE GAUGE) CASE 369C **ISSUE F**

DATE 21 JUL 2015

NOTES:

- IOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-

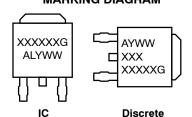
- MENSIONS b3, L3 and Z.

 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
 5. DIMENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

 6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	

GENERIC MARKING DIAGRAM*



XXXXXX = Device Code = Assembly Location Α

L = Wafer Lot Υ = Year WW = Work Week

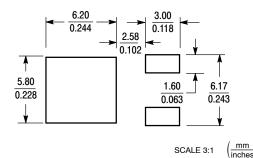
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.

SCALE 1:1 - h3 В L3 Ո DETAIL A NOTE 7 C-**BOTTOM VIEW** e SIDE VIEW | \oplus | 0.005 (0.13) $\overline{\mathbb{M}}$ C **TOP VIEW** Z Ħ L2 GAUGE C SEATING **BOTTOM VIEW** Α1 ALTERNATE CONSTRUCTIONS

STYLE 1:	STYLE 2:	STYLE 3:		STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. GAT	E PIN 1. A	ANODE	PIN 1. CATHODE	PIN 1. GATE
2. COLLE	CTOR 2. DRA	.IN 2. (CATHODE	2. ANODE	2. ANODE
EMITTE	ER 3. SOL	IRCE 3. A	ANODE	3. GATE	CATHODE
COLLE	CTOR 4. DRA	.IN 4. (CATHODE	4. ANODE	4. ANODE
STYLE 6: PIN 1. MT1 2. MT2 3. GATE 4. MT2	STYLE 7: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 8: PIN 1. N/C 2. CATHOI 3. ANODE 4. CATHOI	DE 2. 3.	9: ANODE CATHODE RESISTOR ADJUST CATHODE	STYLE 10: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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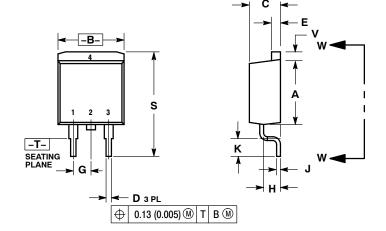
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D²PAK 3 CASE 418B-04 **ISSUE L**

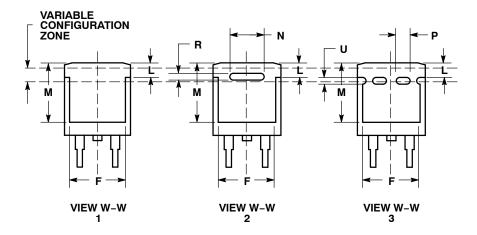
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SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
Р	0.079	REF	2.00 REF	
R	0.039 REF		0.99	REF
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: STYLE 6:

PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE PIN 1. NO CONNECT 2. CATHODE 3. ANODE 4. CATHODE

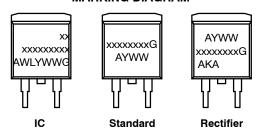
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DATE 17 FEB 2015

GENERIC MARKING DIAGRAM*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

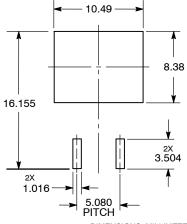
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

SOLDERING FOOTPRINT*



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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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